

## Supporting Information

# Coaxial Multi-shelled TiO<sub>2</sub> Nanotube Arrays for Dye Sensitized Solar Cells

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## Contents:

**Figure S1.** The schematic fabrication procedure of LbL-AR for TiO<sub>2</sub> shells

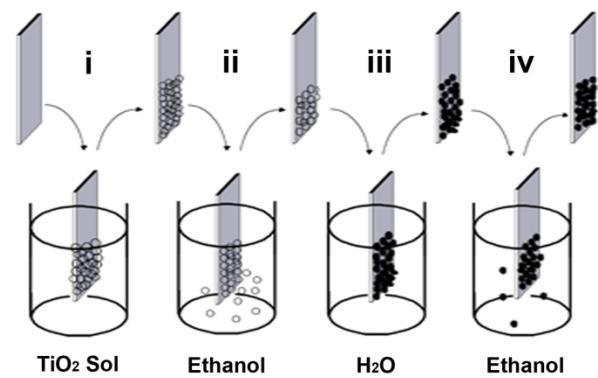
**Figure S2.** The high-magnification FESEM images of ZnO spacing layer and multi-shelled TiO<sub>2</sub> NTs.

**Figure S3.** The typical FESEM and TEM images of multi-shelled TiO<sub>2</sub> NTAs with different shell numbers.

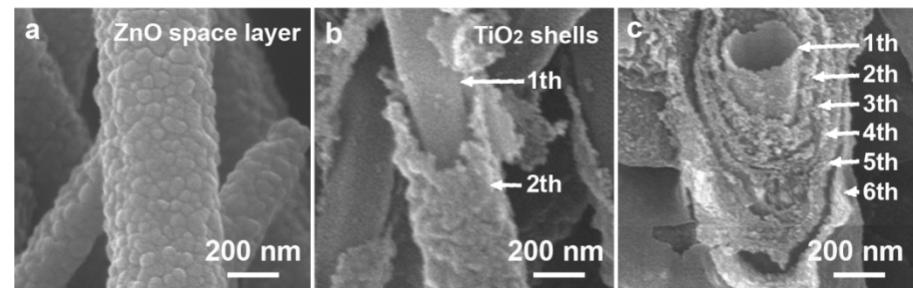
**Figure S4.** Typical high-magnification top-view FESEM images of broken tips of multi-shelled TiO<sub>2</sub> NTs with different shell numbers.

**Figure S6.** The typical characteristics of high-density triple-shelled TiO<sub>2</sub> NTAs.

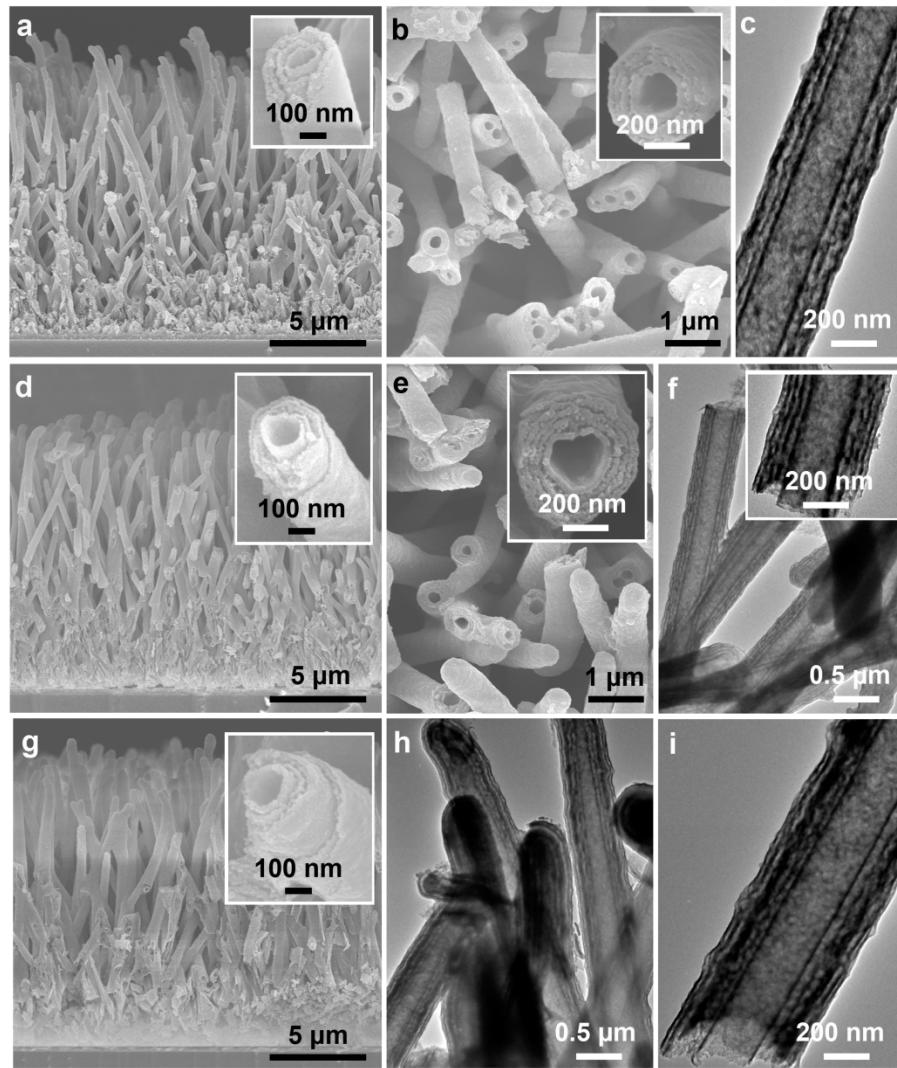
**Figure S6.** The equivalent circuit model of the multi-shelled TiO<sub>2</sub> NTAs DSSCs.



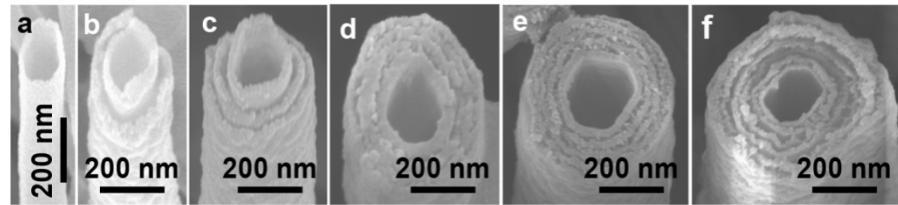
**Figure S1.** The schematic illustration for a cycle of LbL-AR procedure.



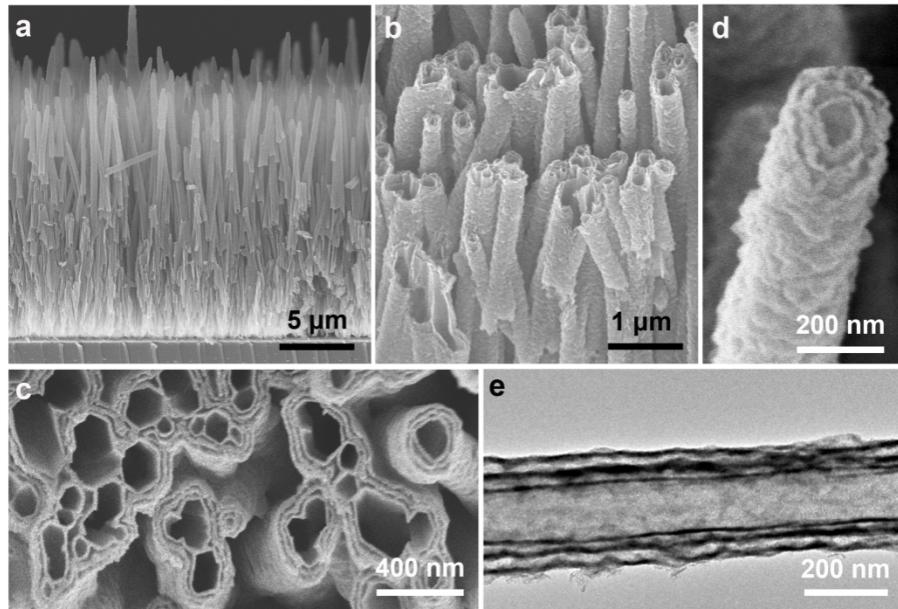
**Figure S2.** The high-magnification FESEM images of (a) ZnO space layer deposited over TiO<sub>2</sub> shells by SG technology, (b) double-shelled TiO<sub>2</sub> NT and (c) sextuple-shelled TiO<sub>2</sub> NTs.



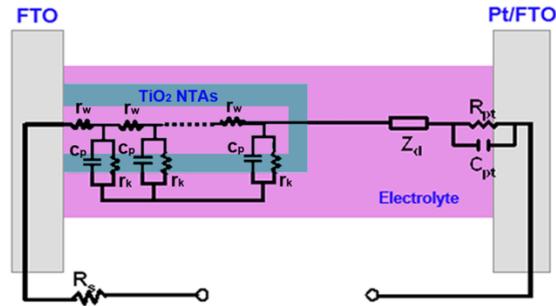
**Figure S3.** The typical FESEM and TEM images of multi-shelled  $\text{TiO}_2$  NTAs with (a-c) quadruple-, (d-f) quintuple- and (g-i) sextuple shells. Low-magnification side-view FESEM images of (a) quadruple, (d) quintuple and (g) sextuple-shelled  $\text{TiO}_2$  NTAs. High-magnification top-view FESEM images of (b) quadruple- and (e) quintuple-shelled  $\text{TiO}_2$  NTAs. Low-magnification TEM images of (f) quintuple- and (h) sextuple-shelled  $\text{TiO}_2$  NTAs. High magnification TEM images of (c) quadruple- and (i) sextuple-shelled  $\text{TiO}_2$  NTs.



**Figure S4.** Typical high-magnification top-view FESEM images of broken tip of multi-shelled TiO<sub>2</sub> NTs with different shell numbers. (a) Single-, (b) double-, (c) triple-, (d) quadruple-, (e) quintuple- and (f) sextuple-shelled TiO<sub>2</sub> NT.



**Figure S5.** The typical characteristics of high-density triple-shelled TiO<sub>2</sub> NTAs. (a) low-, (b) middle magnification side-view FESEM images, (c) high magnification top-view FESEM image captured from broken edges of triple-shelled TiO<sub>2</sub> NTAs. (d) FESEM and (e) TEM images of an individual triple-shelled TiO<sub>2</sub> NT.



**Figure S6.** The equivalent circuit model of the multi-shelled TiO<sub>2</sub> NTAs DSSCs. The simulated electron transport parameters include the electron transport resistance ( $R_w=r_w L$ ,  $r_w$  is component of the equivalent circuit, and  $L$  is the thickness of the multi-shelled TiO<sub>2</sub> NTAs photoanode), recombination resistance ( $R_k=r_k/L$ ,  $r_k$  is component of the equivalent circuit), the capacitance of the electrical double layer ( $C_p=c_p L$ ,  $c_p$  is component of the equivalent circuit), the electron collect efficiency ( $\eta_{cc}=1-R_w/R_k$ ).